

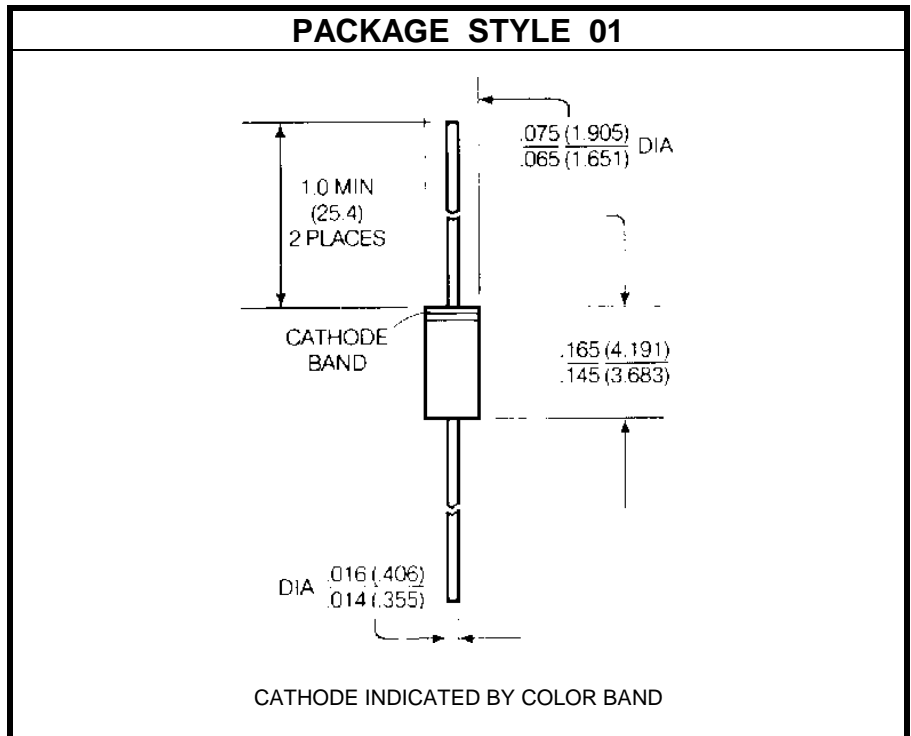
SILICON SCHOTTKY BARRIER DETECTOR DIODE

DESCRIPTION:

The **ASI A2S263** is a Silicon P-Type Schottky Barrier Zero Bias Detector Diode Housed in a Hermetically Sealed Glass Package.

MAXIMUM RATINGS

I_C	20 mA
V_{CE}	2.5 V
P_{DISS}	100 mW @ T _C = 25 °C
T_J	-60 °C to +125 °C
T_{STG}	-60 °C to +125 °C


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIM	UNITS
V _b	I _r = 100 μA	0.5	1.5		V
t _{ss}	F = 10 GHz R _L = 27 KΩ BIAS = NONE B.W. = 375 KHz LOW FREQUENCY CUTOFF = 100 Hz	-59			dBm
V _o	f = 10 GHz P _{in} = -40 dBm BIAS = NONE	5000	8000		μV/μW
R _v		800		6000	Ohms
T _{solid}	t = 5.0 SEC.			+230	°C